Emanuele Pelucchi

List of Publications by Year
in descending order

206 papers	3,689 citations	136950 32 h-index	168389 53 g-index
208 all docs	208 docs citations	208 times ranked	3380 citing authors

#	Article	IF	Citations
1	Towards quantum-dot arrays of entangled photon emitters. Nature Photonics, 2013, 7, 527-531.	31.4	185
2	Probing carrier dynamics in nanostructures by picosecond cathodoluminescence. Nature, 2005, 438, 479-482.	27.8	157
3	Growth and characterization of single quantum dots emitting at 1300 nm. Applied Physics Letters, 2005, 86, 101908.	3.3	153
4	The potential and global outlook of integrated photonics for quantum technologies. Nature Reviews Physics, 2022, 4, 194-208.	26.6	151
5	Hot-Electron Injection in Au Nanorodâ€"ZnO Nanowire Hybrid Device for Near-Infrared Photodetection. Nano Letters, 2014, 14, 6202-6209.	9.1	141
6	Single photon emission from site-controlled pyramidal quantum dots. Applied Physics Letters, 2004, 84, 648-650.	3.3	110
7	III-V-on-Si photonic integrated circuits realized using micro-transfer-printing. APL Photonics, 2019, 4, .	5.7	108
8	Transfer-printing-based integration of a III-V-on-silicon distributed feedback laser. Optics Express, 2018, 26, 8821.	3.4	98
9	Fine structure of exciton complexes in high-symmetry quantum dots: Effects of symmetry breaking and symmetry elevation. Physical Review B, 2010, 81, .	3.2	86
10	Heterogeneous III-V on silicon nitride amplifiers and lasers via microtransfer printing. Optica, 2020, 7, 386.	9.3	84
11	High uniformity of site-controlled pyramidal quantum dots grown on prepatterned substrates. Applied Physics Letters, 2004, 84, 1943-1945.	3.3	79
12	A site-controlled quantum dot system offering both high uniformity and spectral purity. Applied Physics Letters, 2009, 94, 223121.	3.3	78
13	Quantum-dot exciton dynamics probed by photon-correlation spectroscopy. Physical Review B, 2006, 73, .	3.2	55
14	Direct or Indirect Bandgap in Hybrid Lead Halide Perovskites?. Advanced Optical Materials, 2018, 6, 1701254.	7.3	54
15	Symmetries and the Polarized Optical Spectra of Exciton Complexes in Quantum Dots. Physical Review Letters, 2011, 107, 127403.	7.8	52
16	Mechanisms of Quantum Dot Energy Engineering by Metalorganic Vapor Phase Epitaxy on Patterned Nonplanar Substrates. Nano Letters, 2007, 7, 1282-1285.	9.1	51
17	Dense uniform arrays of site-controlled quantum dots grown in inverted pyramids. Applied Physics Letters, 2004, 84, 2907-2909.	3.3	50
18	Microâ€Transferâ€Printed IIIâ€Vâ€onâ€Silicon Câ€Band Semiconductor Optical Amplifiers. Laser and Photonics Reviews, 2020, 14, 1900364.	8.7	50

#	Article	IF	Citations
19	Luttinger-Liquid Behavior in Weakly Disordered Quantum Wires. Physical Review Letters, 2006, 97, 196802.	7.8	48
20	Transition from Two-Dimensional to Three-Dimensional Quantum Confinement in Semiconductor Quantum Wires/Quantum Dots. Nano Letters, 2007, 7, 2227-2233.	9.1	46
21	Optical polarization anisotropy and hole states in pyramidal quantum dots. Applied Physics Letters, 2006, 89, 251113.	3.3	44
22	InP-Based Active and Passive Components for Communication Systems at 2 Î¼m. Journal of Lightwave Technology, 2015, 33, 971-975.	4.6	44
23	Dense WDM transmission at 2â€‰â€‰Î¼m enabled by an arrayed waveguide grating. Optics Letters, 2015, 40, 3308.	3.3	42
24	Selective carrier injection into patterned arrays of pyramidal quantum dots for entangled photon light-emitting diodes. Nature Photonics, 2016, 10, 782-787.	31.4	42
25	Site- and energy-controlled pyramidal quantum dot heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 25, 288-297.	2.7	40
26	Alloy Segregation, Quantum Confinement, and Carrier Capture in Self-Ordered Pyramidal Quantum Wires. Nano Letters, 2006, 6, 1036-1041.	9.1	39
27	AlGaAs/GaAs/AlGaAs quantum wells as a sensitive tool for the MOVPE reactor environment. Journal of Crystal Growth, 2010, 312, 3057-3062.	1.5	38
28	Low Noise Heterogeneous IIIâ€Vâ€onâ€Siliconâ€Nitride Modeâ€Locked Comb Laser. Laser and Photonics Reviews, 2021, 15, 2000485.	8.7	38
29	Decomposition, diffusion, and growth rate anisotropies in self-limited profiles during metalorganic vapor-phase epitaxy of seeded nanostructures. Physical Review B, 2011, 83, .	3.2	36
30	Transfer Printing of AlGaInAs/InP Etched Facet Lasers to Si Substrates. IEEE Photonics Journal, 2016, 8, 1-10.	2.0	36
31	Self-Limiting Evolution of Seeded Quantum Wires and Dots on Patterned Substrates. Physical Review Letters, 2012, 108, 256102.	7.8	35
32	Micro-transfer-printed III-V-on-silicon C-band distributed feedback lasers. Optics Express, 2020, 28, 32793.	3.4	33
33	Electroluminescence from a single pyramidal quantum dot in a light-emitting diode. Applied Physics Letters, 2004, 84, 1967-1969.	3.3	32
34	Single-photon emission from pyramidal quantum dots: The impact of hole thermalization on photon emission statistics. Physical Review B, 2005, 72, .	3.2	31
35	Theory and experiment of step bunching on misoriented GaAs(001) during metalorganic vapor-phase epitaxy. Applied Physics Letters, 2008, 92, 013117.	3.3	31
36	Conditions for entangled photon emission from (111)B site-controlled pyramidal quantum dots. Journal of Applied Physics, 2015, 117, .	2.5	31

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37	Sub-meV photoluminescence linewidth and >106cm2â^•Vs electron mobility in AlGaAsâ^•GaAs quantum wells grown by metalorganic vapor phase epitaxy on slightly misoriented substrates. Journal of Applied Physics, 2006, 99, 093515.	2.5	30
38	40 Gb/s WDM Transmission Over 1.15-km HC-PBGF Using an InP-Based Mach-Zehnder Modulator at 2 Î¼m. Journal of Lightwave Technology, 2016, 34, 1706-1711.	4.6	30
39	Narrow (â‰^4meV) inhomogeneous broadening and its correlation with confinement potential of pyramidal quantum dot arrays. Applied Physics Letters, 2007, 91, 081106.	3.3	29
40	Adhesive bonding for mechanically stacked solar cells. Progress in Photovoltaics: Research and Applications, 2015, 23, 1080-1090.	8.1	28
41	Comparison of InGaAs and InAlAs sacrificial layers for release of InP-based devices. Optical Materials Express, 2017, 7, 4408.	3.0	28
42	Photocapacitance study of bulk deep levels in ZnSe grown by molecular-beam epitaxy. Journal of Applied Physics, 2000, 87, 730-738.	2.5	27
43	High-quality InxGa1â€"xAs/Al0.30Ga0.70As quantum dots grown in inverted pyramids. Physica Status Solidi (B): Basic Research, 2003, 238, 233-236.	1.5	27
44	Remote phonon and surface roughness limited universal electron mobility of In0.53Ga0.47As surface channel MOSFETs. Microelectronic Engineering, 2011, 88, 1083-1086.	2.4	27
45	Single pairs of time-bin-entangled photons. Physical Review A, 2015, 92, .	2.5	26
46	Droplet etching of deep nanoholes for filling with self-aligned complex quantum structures. Nanoscale Research Letters, 2016, 11, 282.	5.7	25
47	Surface organization of homoepitaxial InP films grown by metalorganic vapor-phase epitaxy. Physical Review B, 2012, 86, .	3.2	24
48	Direct visualization of phase-matched efficient second harmonic and broadband sum frequency generation in hybrid plasmonic nanostructures. Light: Science and Applications, 2020, 9, 180.	16.6	24
49	Site-controlled quantum dots grown in inverted pyramids for photonic crystal applications. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 23, 476-481.	2.7	23
50	InAlAs solar cell on a GaAs substrate employing a graded InxGa1â^'xAsâ€"InP metamorphic buffer layer. Applied Physics Letters, 2013, 102, .	3.3	23
51	Lithographically Defined, Room Temperature Low Threshold Subwavelength Red-Emitting Hybrid Plasmonic Lasers. Nano Letters, 2016, 16, 7822-7828.	9.1	23
52	Transfer-print integration of GaAs p-i-n photodiodes onto silicon nitride waveguides for near-infrared applications. Optics Express, 2020, 28, 21275.	3.4	23
53	Chemical and electrical characterization of the HfO2/InAlAs interface. Journal of Applied Physics, 2013, 114, .	2.5	22
54	Local interface composition and native stacking fault density in ZnSeâ^•GaAs(001) heterostructures. Journal of Applied Physics, 2004, 96, 2592-2602.	2.5	21

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55	Enhancement of the binding energy of charged excitons in disordered quantum wires. Physical Review B, 2005, 71, .	3.2	21
56	Excited excitonic states observed in semiconductor quantum dots using polarization resolved optical spectroscopy. Journal of Applied Physics, 2007, 101, 081703.	2.5	20
57	Coulomb correlations of charged excitons in semiconductor quantum dots. Physical Review B, 2009, 80, .	3.2	18
58	Access resistance reduction in Ge nanowires and substrates based on non-destructive gas-source dopant in-diffusion. Journal of Materials Chemistry C, 2014, 2, 9248-9257.	5.5	18
59	Time-resolved cathodoluminescence of InGaAs/AlGaAs tetrahedral pyramidal quantum structures. Applied Physics B: Lasers and Optics, 2006, 84, 343-350.	2.2	17
60	Pyramidal<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>GaAs</mml:mtext><mml:mo>/</mml:mo><mml:msub><mml:mrow><mml:mtext>Al</mml:n wire/dot systems with controlled heterostructure potential. Physical Review B, 2010, 82, .	3.2	17
61	Suppression of threading defects formation during Sb-assisted metamorphic buffer growth in InAs/InGaAs/InP structure. Applied Physics Letters, 2012, 100, .	3.3	17
62	Thermal Analysis of InP Lasers Transfer Printed to Silicon Photonics Substrates. Journal of Lightwave Technology, 2018, 36, 5935-5941.	4.6	17
63	Controlling the native stacking fault density in II-VI/III-V heterostructures. Applied Physics Letters, 2003, 83, 81-83.	3.3	16
64	Control of valence band states in pyramidal quantum dot-in-dot semiconductor heterostructures. Applied Physics Letters, 2007, 91, .	3.3	16
65	Hybridization of Electron and Hole States in Semiconductor Quantumâ€Dot Molecules. Small, 2009, 5, 329-335.	10.0	16
66	Growth and structural characterization of pyramidal siteâ€controlled quantum dots with high uniformity and spectral purity. Physica Status Solidi (B): Basic Research, 2010, 247, 1862-1866.	1.5	16
67	Correlation between optical properties and interface morphology of GaAsâ^•AlGaAs quantum wells. Applied Physics Letters, 2006, 88, 141917.	3.3	15
68	Optimization of the efficiency of single-photon sources based on quantum dots under optical excitation. Applied Physics Letters, 2006, 88, 081905.	3.3	15
69	InGaAs Surface Normal Photodiode for 2 <inline-formula> <tex-math notation="LaTeX">$mu ext{m}$ </tex-math></inline-formula> Optical Communication Systems. IEEE Photonics Technology Letters, 2015, 27, 1469-1472.	2.5	15
70	Evidence for a dominant midgap trap in n-ZnSe grown by molecular beam epitaxy. Applied Physics Letters, 1999, 75, 832-834.	3.3	13
71	Low-angle misorientation dependence of the optical properties of InGaAs/InAlAs quantum wells. Journal of Crystal Growth, 2010, 312, 1546-1550.	1.5	13
72	Microtopography of the eye surface of the crab <i>Carcinus maenas</i> : an atomic force microscope study suggesting a possible antifouling potential. Journal of the Royal Society Interface, 2013, 10, 20130122.	3.4	13

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73	10 Gb/s InP-based Mach-Zehnder modulator for operation at 2 Î¼m wavelengths. Optics Express, 2015, 23, 10905.	3.4	13
74	Complex optical signatures from quantum dot nanostructures and behavior in inverted pyramidal recesses. Physical Review B, 2014, 89, .	3.2	12
75	Native oxides formation and surface wettability of epitaxial IIIâ€“V materials: The case of InP and GaAs. Applied Surface Science, 2016, 383, 19-27.	6.1	12
76	Exploring conductivity in ex-situ doped Si thin films as thickness approaches 5â€‰nm. Journal of Applied Physics, 2019, 125, 225709.	2.5	12
77	Spin-resolved electron spectroscopy with highly polarized sources: Inverse photoemission from ferromagnets. Review of Scientific Instruments, 1997, 68, 1841-1845.	1.3	11
78	Patterning of confined-state energies in site-controlled semiconductor quantum dots. Applied Physics Letters, 2005, 86, 243105.	3.3	11
79	Physics of novel site controlled InGaAs quantum dots on (111) oriented substrates. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2761-2764.	2.7	11
80	Self-ordered nanostructures on patterned substrates. Journal of Materials Science: Materials in Electronics, 2018, 29, 952-967.	2.2	11
81	Vanishing biexciton binding energy from stacked, MOVPE grown, site-controlled pyramidal quantum dots for twin photon generation. Journal of Crystal Growth, 2019, 506, 36-39.	1.5	11
82	Impact of nitrogen incorporation on pseudomorphic site-controlled quantum dots grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2010, 97, .	3.3	10
83	Spectral signatures of high-symmetry quantum dots and effects of symmetry breaking. New Journal of Physics, 2015, 17, 103017.	2.9	10
84	Indium segregation during IIIâ€“V quantum wire and quantum dot formation on patterned substrates. Journal of Applied Physics, 2015, 117, 164313.	2.5	10
85	Structural and electronic properties of ZnSe/AlAs heterostructures. Physical Review B, 2001, 63, .	3.2	9
86	Properties of GaAs/AlGaAs quantum wells grown by MOVPE using vicinal GaAs substrates. Journal of Crystal Growth, 2004, 272, 615-620.	1.5	9
87	Wettability and â€œpetal effectâ€• of GaAs native oxides. Journal of Applied Physics, 2011, 110, .	2.5	9
88	Fine-structure splitting in large-pitch pyramidal quantum dots. Physical Review B, 2012, 85, .	3.2	9
89	Ideal unreactive metal/semiconductor interfaces:â€ƒThe case ofZn/ZnSe(001). Physical Review B, 2001, 63, .	3.2	8
90	Localization of excitons in disordered quantum wires probed by single-photon correlation spectroscopy. Applied Physics Letters, 2004, 85, 5715-5717.	3.3	8

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91	Crystal defect topography of Stranskiâ€“Krastanow quantum dots by atomic force microscopy. Applied Physics Letters, 2010, 97, .	3.3	8
92	A study of nitrogen incorporation in pyramidal site-controlled quantum dots. Nanoscale Research Letters, 2011, 6, 567.	5.7	8
93	Compact Electroabsorption Modulators for Photonic Integrated Circuits, Using an Isolated Pedestal Contact Scheme. IEEE Photonics Technology Letters, 2012, 24, 356-358.	2.5	8
94	Transient and self-limited nanostructures on patterned surfaces. Physical Review B, 2013, 87, .	3.2	8
95	AlInGaAs surface normal photodiode for 2 Âµm optical communication systems. , 2015, , .		8
96	Atomic ordering and bond relaxation in optical spectra of self-organized InP/GaInP2 Wigner molecule structures. Applied Physics Letters, 2019, 115, .	3.3	8
97	Edge-Coupling of O-Band InP Etched-Facet Lasers to Polymer Waveguides on SOI by Micro-Transfer-Printing. IEEE Journal of Quantum Electronics, 2020, 56, 1-8.	1.9	8
98	ZnSe/CdTe/ZnSe heterostructures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2263.	1.6	7
99	Phonon replicas of charged and neutral exciton complexes in single quantum dots. Physical Review B, 2010, 82, .	3.2	7
100	Relevance of the purity level in a MetalOrganic Vapour Phase Epitaxy reactor environment for the growth of high quality pyramidal site-controlled Quantum Dots. Journal of Crystal Growth, 2011, 315, 119-122.	1.5	7
101	Semiconductor nanostructures engineering: Pyramidal quantum dots. Current Opinion in Solid State and Materials Science, 2012, 16, 45-51.	11.5	7
102	Evidence of nonadiabatic exciton-phonon interaction probed by second-order LO-phonon replicas of single quantum dots. Physical Review B, 2013, 87, .	3.2	7
103	Unusual nanostructures of â€œlattice matchedâ€•InP on AlInAs. Applied Physics Letters, 2014, 104, 141606.	3.3	7
104	Spin polarized photoemission from thin GaAs photocathodes. Journal of Electron Spectroscopy and Related Phenomena, 1995, 76, 505-509.	1.7	6
105	Tunable Schottky barrier contacts to In[sub x]Ga[sub 1â^'x]As. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2119.	1.6	6
106	Structural and electronic properties of wide band gap Zn1â^'xMgxSe alloys. Journal of Applied Physics, 2004, 95, 4184-4192.	2.5	6
107	Step ordering induced by nonplanar patterning of GaAs surfaces. Applied Physics Letters, 2006, 88, 203104.	3.3	6
108	Quantum dot molecules realized with modulated quantum wire heterostructrues. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1815-1818.	2.7	6

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109	Exciton-phonon coupling in single quantum dots with different barriers. Applied Physics Letters, 2011, 98, .	3.3	6
110	On the activation of implanted silicon ions inp-In0.53Ga0.47As. Semiconductor Science and Technology, 2012, 27, 082001.	2.0	6
111	Statistical study of stacked/coupled site-controlled pyramidal quantum dots and their excitonic properties. Applied Physics Letters, 2017, 111, .	3.3	6
112	Tuning InP self-assembled quantum structures to telecom wavelength: A versatile original InP(As) nanostructure â€œworkshopâ€. Applied Physics Letters, 2017, 110, 113101.	3.3	6
113	Microtransfer Printing Highâ€Efficiency GaAs Photovoltaic Cells onto Silicon for Wireless Power Applications. Advanced Materials Technologies, 2020, 5, 2000048.	5.8	6
114	Optical properties and symmetry optimization of spectrally (excitonically) uniform site-controlled GaAs pyramidal quantum dots. Applied Physics Letters, 2021, 118, .	3.3	6
115	Band discontinuities in ZnMgSe/ZnCdSe(001) lattice-matched heterostructures. Applied Physics Letters, 2001, 78, 1574-1576.	3.3	5
116	On the calculation of effective electric field in In0.53Ga0.47As surface channel metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2011, 98, 193501.	3.3	5
117	High index contrast optical platform using gallium phosphide on sapphire: an alternative to SOI?. Proceedings of SPIE, 2012, , .	0.8	5
118	SiNx-induced intermixing in AlInGaAs/InP quantum well through interdiffusion of group III atoms. Journal of Applied Physics, 2012, 112, .	2.5	5
119	Morphological, compositional, and geometrical transients of V-groove quantum wires formed during metalorganic vapor-phase epitaxy. Applied Physics Letters, 2013, 103, .	3.3	5
120	Quantum dot asymmetry and the nature of excited hole states probed by the doubly positively charged exciton<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msup><mml:mi>X</mml:mi><mml:mrow><mml:mn>2</mml:mn><mml:mo>+</mml:mo></mml:mrow></mml:m Physical Review B, 2013, 88, .	3.2	5
121	Evaluation of defect density by top-view large scale AFM on metamorphic structures grown by MOVPE. Applied Surface Science, 2015, 349, 849-854.	6.1	5
122	Low-power-consumption optical interconnect on silicon by transfer-printing for used in opto-isolators. Journal Physics D: Applied Physics, 2019, 52, 064001.	2.8	5
123	Growth and optical characterization of dense arrays of site-controlled quantum dots grown in inverted pyramids. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 193-198.	2.7	4
124	Correlated photon emission from semiconductor quantum dots grown in inverted pyramids. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 194-198.	2.7	4
125	Pyramidal quantum dots: High uniformity and narrow excitonic emission. Superlattices and Microstructures, 2010, 47, 78-82.	3.1	4
126	Optics, morphology, and growth kinetics of GaAs/AlxGa1â^'xAs quantum wells grown on vicinal substrates by metalorganic vapor phase epitaxy. Physical Review B, 2011, 84, .	3.2	4

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127	Sub 10 ps Carrier Response Times in Electroabsorption Modulators Using Quantum Well Offsetting. IEEE Journal of Quantum Electronics, 2012, 48, 1467-1475.	1.9	4
128	Semiconductor Quantum Well Lasers With a Temperature-Insensitive Threshold Current. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 177-182.	2.9	4
129	Unexpected Aspects of Strain Relaxation and Compensation in InGaAs Metamorphic Structures Grown by MOVPE. Crystal Growth and Design, 2016, 16, 2363-2370.	3.0	4
130	Three-Dimensional Self-Assembled Columnar Arrays of AlInP Quantum Wires for Polarized Micrometer-Sized Amber Light Emitting Diodes. ACS Photonics, 2018, 5, 1318-1325.	6.6	4
131	Contactless electroreflectance study of the surface potential barrier in <i>n</i>-type and <i>p</i>-type InAlAs van Hoof structures lattice matched to InP. Journal Physics D: Applied Physics, 2018, 51, 215104.	2.8	4
132	AsH3 gas-phase <i>ex situ</i> doping 3D silicon structures. Journal of Applied Physics, 2018, 124, .	2.5	4
133	Next generation low temperature polycrystalline materials for above IC electronics. High mobility n- and p-type IIIâ€“V metalorganic vapour phase epitaxy thin films on amorphous substrates. JPhys Photonics, 2020, 2, 025003.	4.6	4
134	Early stages of InP nanostructure formation on AlInAs. Physical Review B, 2020, 101, .	3.2	4
135	CdTe epitaxial layers in ZnSe-based heterostructures. Journal of Crystal Growth, 1999, 201-202, 465-469.	1.5	3
136	Controlling interface reactivity and Schottky barrier height in Auâˆ•ZnSe(001) junctions. Journal of Vacuum Science & Technology B, 2006, 24, 1259.	1.3	3
137	Physical properties of highly uniform InGaAs pyramidal quantum dots with GaAs barriers: Fine structure splitting in pre-patterned substrates. Superlattices and Microstructures, 2011, 49, 279-282.	3.1	3
138	Optical characterization of individual quantum dots. Physica B: Condensed Matter, 2012, 407, 1472-1475.	2.7	3
139	Polarizers in an Asymmetric Twin Waveguide Based on Resonant Coupling. IEEE Photonics Technology Letters, 2013, 25, 1301-1304.	2.5	3
140	Excitonic lasing of strain-free InP(As) quantum dots in AlInAs microdisk. Applied Physics Letters, 2017, 110, .	3.3	3
141	Low Threshold Lasing in InP/GaInP Quantum Dot Microdisks. Semiconductors, 2018, 52, 1894-1897.	0.5	3
142	Biexciton initialization by two-photon excitation in site-controlled quantum dots: The complexity of the antibinding state case. Applied Physics Letters, 2020, 117, 134001.	3.3	3
143	Structural and Electronic Properties of Polycrystalline InAs Thin Films Deposited on Silicon Dioxide and Glass at Temperatures below 500 Â°C. Crystals, 2021, 11, 160.	2.2	3
144	High Hole Mobility Polycrystalline GaSb Thin Films. Crystals, 2021, 11, 1348.	2.2	3

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145	Influence of long-range substrate roughness on disorder in V-groove quantum wire structures. Journal of Applied Physics, 2006, 100, 123509.	2.5	2
146	Dielectric-Free Fabrication of Compact 30-GHz Photodetectors Using the Isolated Pedestal Contact Configuration. IEEE Photonics Technology Letters, 2012, 24, 1082-1084.	2.5	2
147	Electrical characterisation of InGaAs on insulator structures. Microelectronic Engineering, 2015, 147, 63-66.	2.4	2
148	AlGaAs ridge laser with 33% wall-plug efficiency at 100 Â°C based on a design of experiments approach. Semiconductor Science and Technology, 2016, 31, 045002.	2.0	2
149	Study of electro-optic effect in asymmetrically ramped AlInGaAs multiple quantum well structures. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 930-935.	1.8	2
150	III-V-on-silicon widely tunable laser realized using micro-transfer-printing. , 2019, , .		2
151	Importance of Overcoming MOVPE Surface Evolution Instabilities for >1.3 Î¼m Metamorphic Lasers on GaAs. Crystal Growth and Design, 2021, 21, 2068-2075.	3.0	2
152	Engineering site-controlled quantum dots for optical quantum information processing. , 2019, , .		2
153	Impact of DWDM at 50GHz spacing in the 2Âµm waveband. , 2016, , .		2
154	On-chip optical interconnect on silicon by transfer printing. , 2018, , .		2
155	Transfer-printing for heterogeneous integration. , 2019, , .		2
156	Excitonic properties and band alignment in lattice-matched ZnCdSe/ZnMgSe multiple-quantum-well structures. Applied Physics Letters, 2001, 78, 434-436.	3.3	1
157	Observation of charged excitons in V-groove quantum wires. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 526-530.	0.8	1
158	Epitaxial Al/GaN and Au/GaN junctions on as-grown GaN(0001)1 Ã— 1 surfaces. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 804-807.	1.8	1
159	Magneto-photoluminescence of heavy- and light-hole excitons in site-controlled pyramidal quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1873-1875.	2.7	1
160	Design of single growth epitaxial structures for monolithic integration of single frequency laser and Electro-absorption modulators. , 2009, , .		1
161	Nitrogen Incorporation Effects On Site-Controlled Quantum Dots. , 2011, , .		1
162	High speed AlInGaAs/InGaAs quantum well waveguide photodiode for wavelengths around 2 microns. , 2012, , .		1

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163	Monte Carlo simulation of photonic state tomography: a virtual Hanbury Brown and Twiss correlator. European Journal of Physics, 2016, 37, 034002.	0.6	1
164	Lasing of InP/AlInAs quantum dots in AlInAs microdisk cavity. Journal of Physics: Conference Series, 2016, 690, 012023.	0.4	1
165	Exploring a new transmission window for telecommunications in the 2 Âµm waveband. , 2016, , .		1
166	High-Index-Contrast Î» â€‰ =â€‰ 1.55â€‰Î¼m AlInGaAs/InP Laser Heterostructure Waveguides Through Selective Core Oxidation. Physica Status Solidi (A) Applications and Materials Science, 2018, 216, 1800495.	1.8	1
167	Micro-transfer-printing of InP Photonic Devices to Silicon Photonics. , 2019, , .		1
168	Micro-Transfer-Printed III-V-on-Silicon C-Band SOAs with 17 dB Gain. , 2019, , .		1
169	On-demand single-photons from electrically-injected site-controlled pyramidal quantum dots. Journal Physics D: Applied Physics, 2019, 52, 045107.	2.8	1
170	Tertiarybutylarsine damage-free thin-film doping and conformal surface coverage of substrate-released horizontal Si nanowires. Applied Surface Science, 2020, 508, 145147.	6.1	1
171	Planar Semiconductor Membranes with Brightness Enhanced Embedded Quantum Dots via Electron Beam Induced Deposition of 3D Nanostructures: Implications for Solid State Lighting. ACS Applied Nano Materials, 2020, 3, 12401-12407.	5.0	1
172	Pâ€substrate InPâ€based 1.5 Î¼m lasers using an internal carbonâ€doped layer to block pâ€dopant diffusion. Microwave and Optical Technology Letters, 2018, 60, 2363-2367.	1.4	1
173	An intuitive protocol for polarization-entanglement restoral of quantum dot photon sources with non-vanishing fine-structure splitting. Scientific Reports, 2022, 12, 4723.	3.3	1
174	Electrical properties of n-n ZnSe/In0.04Ga0.96As(001) heterojunctions. Applied Physics Letters, 1998, 73, 2033-2035.	3.3	0
175	Charged excitons in modulation-doped quantum wires. AIP Conference Proceedings, 2005, , .	0.4	0
176	Fermi Liquid Behavior of GaAs Quantum Wires. , 0, , 77-85.		0
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